

**Silicon PNP transistor epitaxial type
B5858**

[Applications]

Portable radio 2W output amplifier of class-B push-pull operation
Medium power switching and muting

[Feature]

Correspond to SS8550
High collector current IC= -1.5A
Complimentary pair with phenitec P/N D5858

[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	-40	V
Collector-emitter voltage	VCEO	-25	V
Emitter-base voltage	VEBO	-6	V
Collector current	IC	-1.5	A
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	-40	-	-	V	IC= -100uA, IE= 0A
Collector-emitter breakdown voltage	BVCEO	-25	-	-	V	IC= -2mA, IB= 0A
Emitter-base breakdown voltage	BVEBO	-6	-	-	V	IE= -100uA, IC= 0A
Collector cut-off current	ICBO	-	-	-100	nA	VCB= -40V, IE= 0A
Emitter cut-off current	IEBO	-	-	-100	nA	VEB= -6V, IE= 0A
DC current gain 1	hFE 1	45	-	-	-	VCE= -1V, IC= -5mA
DC current gain 2	hFE 2	85	160	300	-	VCE= -1V, IC= -100mA
DC current gain 3	hFE 3	40	-	-	-	VCE= -1V, IC= -800mA
Collector-emitter saturation voltage	VCE(sat)	-	-0.28	-0.5	V	IC= -800mA, IB= -80mA
Base-emitter saturation voltage	VBE(sat)	-	-0.98	-1.2	V	IC= -800mA, IB= -80mA
Base-emitter on voltage	VBE(on)	-	-0.66	-1	V	VCE= -1V, IC= -10mA
Transition frequency	fT	100	270	-	MHz	VCE= -10V, IE= 50mA
Collector output capacitance	Cob	-	6.5	-	pF	VCB= -10V, f = 1MHz, IE= 0A

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

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